

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR) same (n p) adj type adj semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 13:38
L2	74	(ferromagnetic adj2 semiconductor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 13:38
L3	25	(tunneling adj (magnetoresistance magnetoresistive (magnetic magneto) adj (resistive resistance)) TMR) same (n p) adj type adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 13:39
S19	1640	(365/158).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 14:10
S20	562	S19 and TMR	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S21	191	S20 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:37
S22	1	10/518391	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S23	44	TMR same (pn "p-n") adj junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:42
S24	22	S23 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S25	2	("6778425").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 14:10
S26	583	ferromagnetic near2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:55

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S27	68	S26 and TMR	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S28	8	S27 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S29	2	("20020057594").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 14:10
S30	369	ferromagnetic adj2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 13:38
S31	165	S30 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 14:10
S32	6	(tunneling adj (magnetoresistance magneto adj resistance TMR)) same half adj metallic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:28
S33	2	(tunneling adj (magnetoresistance magneto adj resistance TMR)) same (n p) adj type adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:29
S34	4	(tunneling adj (magnetoresistance (magnetic magneto) adj resistance TMR)) same (n p) adj type adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:29
S35	6	(tunneling adj (magnetoresistance (magnetic magneto) adj resistance TMR)) same (pn p adj n pin) adj junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:27
S36	1	2002-86928	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:25
S37	47	(tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR) same (pn p adj n pin) adj junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:13

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S38	3	S37 not S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:28
S39	23	(tunneling adj (magnetoresistance magneto adj resistance) TMR) same half adj metallic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:30
S41	23	(tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR) same (n p) adj type adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 13:38
S42	759	(257/E43.004).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 17:34
S44	117	S42 and (tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:57
S45	55	S44 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:57
S46	27	S19 and ferromagnetic adj2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:56
S47	2128	(365/145).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 17:56
S48	15	S47 and ferromagnetic adj2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:56
S49	28	S47 and (tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:58
S50	10	S49 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 17:59

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S51	2101	(257/295).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 17:58
S52	182	S51 and (tunneling adj (magnetoresistance (magnetic magneto) adj resistance) TMR)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:41
S54	43	S52 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:14
S55	70	(tunneling adj (magnetoresistance (magnetic magneto) adj resistance) (ferromagnetic magnetic) near (tunnel adj junction) MJT TMR) same (pn p adj n pin) adj junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:14
S56	23	S55 not S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:14
S57	18	S56 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:26
S58	88	(257/E21.663).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 18:16
S59	806	(257/E21.664).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 18:16
S60	477	(257/E21.665).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/09/29 18:16
S61	337	S60 and (@ad<"20020618" @rlad<"20020618")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/29 18:26
S62	782	(257/421).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/01 10:41

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S63	153	(257/425).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/01 11:14
S64	13	(magneto adj (resistance resistive) magnetoresistance magnetoresistive) with (pn "p-n") adj junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:54
S65	2	("5962905").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/01 10:43
S66	7	("5962905").URPN.	USPAT	OR	ON	2006/10/01 10:44
S67	333	(hiroshi near3 yoshida).in.	USPAT	OR	ON	2006/10/01 10:45
S68	21	(kazunori near3 sato).in.	USPAT	OR	ON	2006/10/01 10:45
S69	3	S67 and (ferromagnetic ferromagnetism)	USPAT	OR	ON	2006/10/01 10:48
S70	583	ferromagnetic near2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:46
S71	7	("5962905").URPN.	USPAT	OR	ON	2006/10/01 10:47
S72	4	("4700211"   "5262666"   "5329480"   "5416353").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/01 10:48
S73	58	(tanaka near3 hidekazu).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/01 10:49
S74	0	S73 and (ferromagnetic ferromagnetism)	USPAT	OR	ON	2006/10/01 10:50
S75	391	(tanaka near3 hidekazu).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:49
S77	6	S75 and (ferromagnetic ferromagnetism)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 10:50
S78	4	("4700211"   "5262666"   "5329480"   "5416353").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/01 10:50
S79	7	("5962905").URPN.	USPAT	OR	ON	2006/10/01 10:50
S80	9	(magnetoresistance TMR) same half adj metallic same barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/01 11:43
S81	3	("7102923").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/01 11:43